



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

S2AB-6AF~S2MB-6AF

SMB General Purpose Rectifier Diode 通用整流二极管

■Features 特点

Low forward voltage drop 低正向压降
Low reverse leakage current 低反向漏电流
High surge current capability 高浪涌电流能力
Surface mount device 表面贴装器件
Case 封装:SMB

HF **RoHS**



■Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	S2AB -6AF	S2BB -6AF	S2DB -6AF	S2GB -6AF	S2JB -6AF	S2KB -6AF	S2MB -6AF	Unit 单位
Marking 印字		S2A	S2B	S2D	S2G	S2J	S2K	S2M	
Peak Reverse Voltage 反向峰值电压	V_{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	V_R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I_F	2							A
Peak Surge Current 峰值浪涌电流	I_{FSM}	60							A
Thermal Resistance J-L 结到管脚热阻	$R_{\theta JL}$	16							$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结/储藏温度	T_J, T_{stg}	$150^{\circ}\text{C}, -55^{\circ}\text{C to } +150^{\circ}\text{C}$							

■Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Test Condition 测试条件
Forward Voltage 正向电压	V_F			1.1	V	$I_F=2\text{A}$
Reverse Current($T_A=25^{\circ}\text{C}/$) 反向电流($T_A=125^{\circ}\text{C}/$)	I_R			5 200	μA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D		30		pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD

CHARACTERISTICS

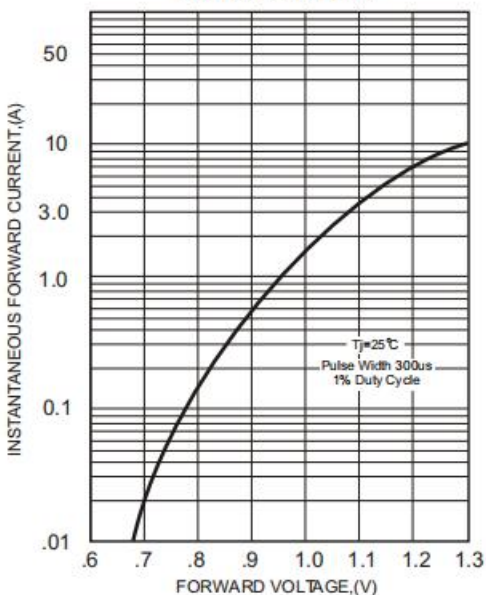


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

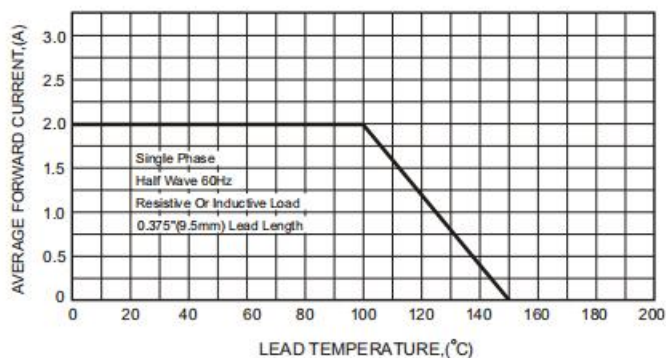


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

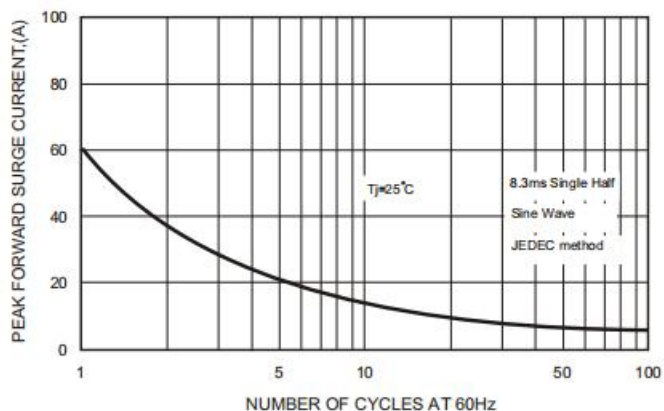


FIG.3 - TYPICAL REVERSE

CHARACTERISTICS

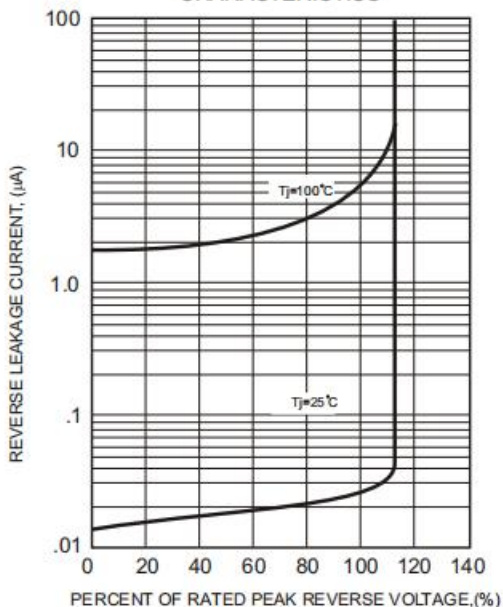
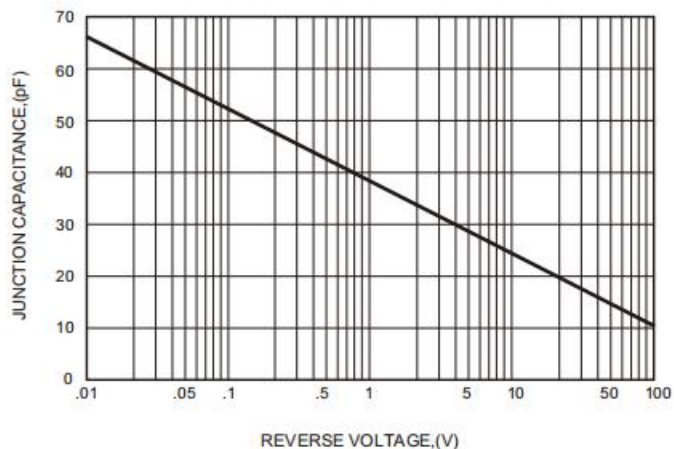
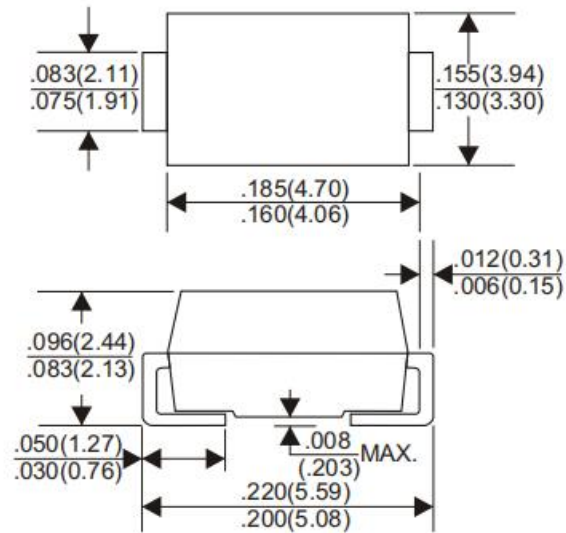


FIG.5-TYPICAL JUNCTION CAPACITANCE



■Dimension 外形封装尺寸

DO-214AA(SMB)



Dimensions in inches and (millimeters)